

**JST132N2-600D 0.5A TRIAC**

Rev.A.1.1

The JST132N2-600D triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Package SOT-89-2L is RoHS compliant.

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c=84^\circ\text{C}$)	$I_{T(RMS)}$	0.5	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	6	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		6.6	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	0.18	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	-	50	A/s
	-	20	
Peak gate current ($t_p=20\text{ }\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	1	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.1	W

Peak gate power op0.48;>BDCID 8 351.192MP

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	10	mA
				20	
I_H	$I_T=50mA$		MAX.	10	mA
dV/dt	$V_D=400V$ Gate Open $T_j=110$		MIN.	60	V s
$(dV/dt)_c$	$(dI/dt)_c=0.3A/ms, T_j=110$		MIN.	5	
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2.5	s
t_{off}				25	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=0.85A t_p=380 s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.98	V
R_D	Dynamic resistance	$T_j=125$	362	
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
I_{RRM}		$T_j=125$	0.15	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	60	$\text{}/W$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=5cm^2$)	100	$\text{}/W$

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

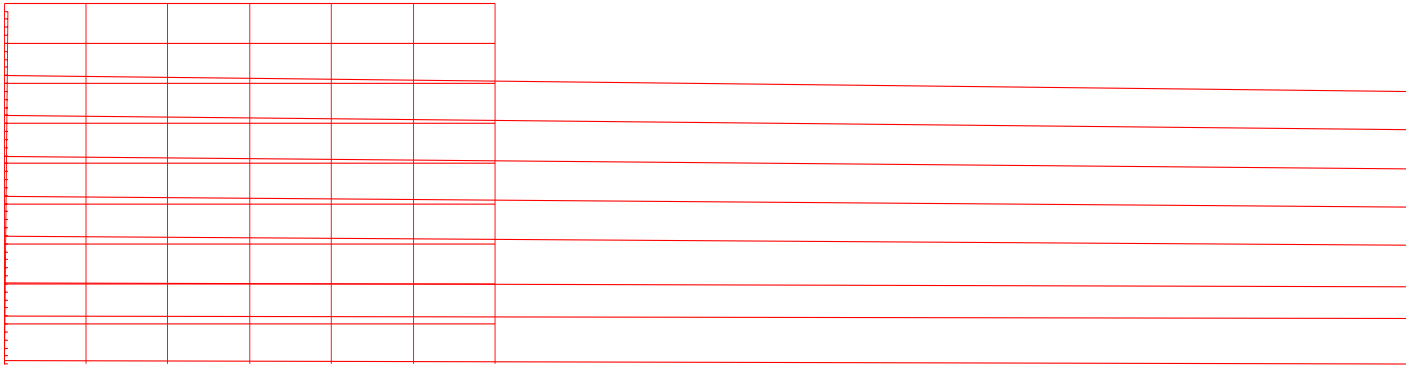


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

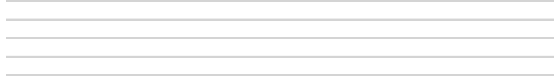
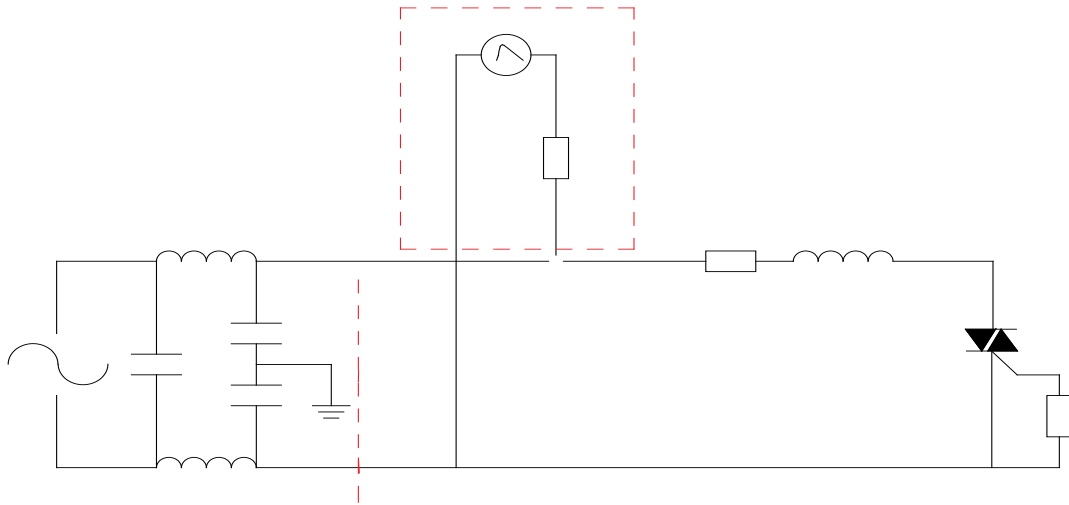
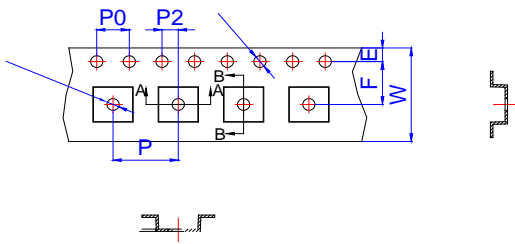


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50			0.059		
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W			12.30			0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95	0.069	0.073	0.076
t	0.20	0.25	0.30	0.008	0.010	0.012
	3°		5°	3°		5°

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